



ELECTRICAL CHARACTERISTICS: OM200L120CMC (Tc= 25°C unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max	Unit
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OFF CHARACTERISTICS

Collector Emitter Breakdown Voltage, VCE=0V	VCES	1200			V
Zero Gate Voltage Drain Current, VGE=0, VCE =1200V	ICES		2		μA
Gate Emitter Leakage Current, VGE=+/-15V, VCE=0V	IGES		100		μA

ON CHARACTERISTICS

Gate Threshold Voltage, VCE=VGE, IC=6mA	VGE(TH)	4.5	5.5	6.5	V
Collector Emitter Saturation Voltage, VGE=15V, IC=200A	VCE(SAT)			2.6	V

DYNAMIC CHARACTERISTICS

Fwd. Transconductance	VCE=5V, IC=200A	gfs	17		S
Input Capacitance	VGE=0	Cies		17	nF
Output Capacitance	VCE=25V	Coes		3	nF
Rev. Transfer Capacitance	f=1.0MHz	Cres		1.5	nF

SWITCHING INDUCTIVE LOAD CHARACTERISTICS

Turn-On Delay Time	VCC= 600V, IC=200A VGE=+15/-10V, RG=5.1Ω L=100μH	t(on)		400	nS
Rise Time		tr		300	nS
Turn-on Losses		Eon			mJ
Turn-off Delay Time		td(off)		700	nS
Fall Time		tf		250	nS
Turn-off Losses		Eoff			mJ

DIODE CHARACTERISTICS

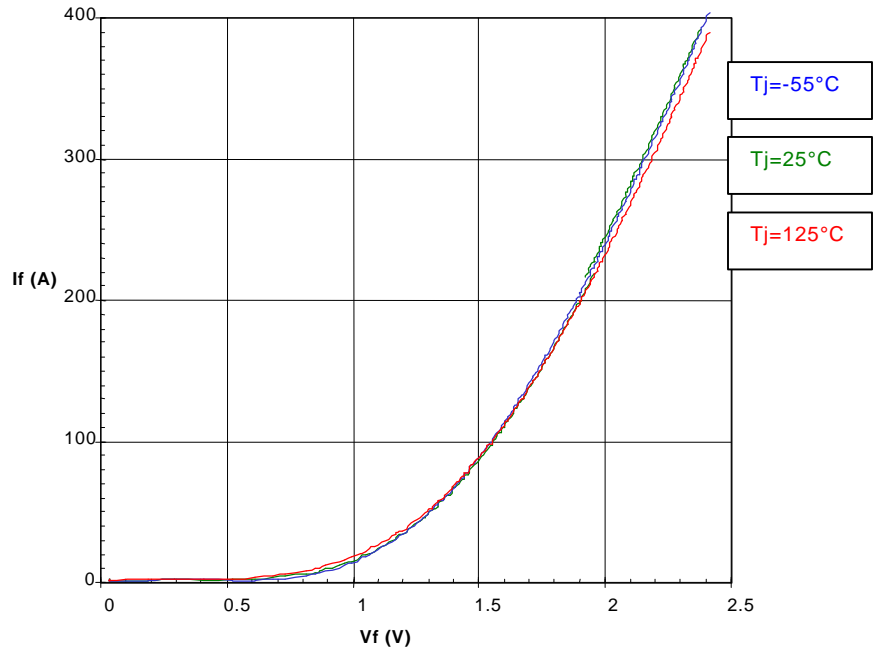
Maximum Forward Voltage	IF=200A, Tj=25°C Tj=125°C	VF		2.0	2.8	V
Reverse Recovery Characteristics	VR=600V, Tj=25°C IF=200A, Tj=125°C di/dt=-1500A/μS Tj=25°C Tj=125°C Tj=25°C Tj=125°C	Qrr		10	2.3	μC
			Irr		15	
				75		
				90		
		trr		100		nS
	150					

THERMAL AND MECHANICAL CHARACTERISTICS

Thermal Resistance, Junction to Case (Per IGBT)		RthJC		0.07	°C/W
Thermal Resistance, Junction to Case (Per Diode)		RthJC		0.12	°C/W
Maximum Junction Temperature		TjMAX		150	°C
Isolation Voltage		ViSRMS		2500	V
Screw Torque	Mounting	-	15	20	in-lb
Screw Torque (M6)	Terminals	-	10	15	in-lb
Screw Torque (M3)	Terminals	-	6	8	in-lb
Module Weight		-	320		Grams

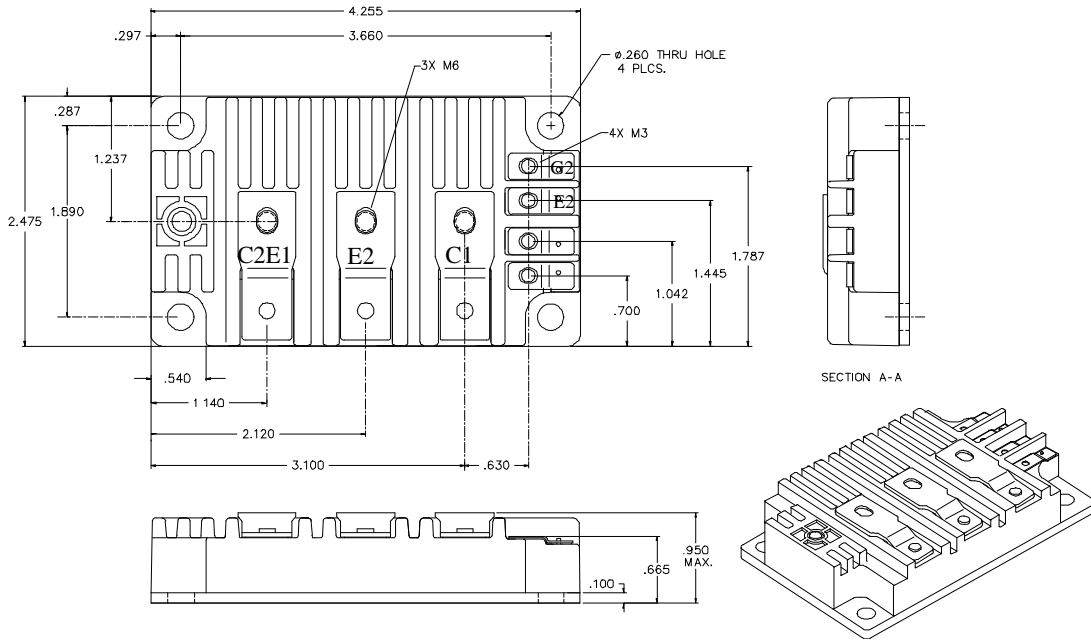
OM200L120CMC

Diode Forward Current vs. Forward Voltage
Vge =0V



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MECHANICAL OUTLINE



EQUIVALENT CIRCUIT

